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Ulf Mattsson et al.

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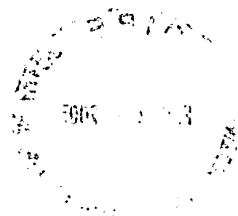
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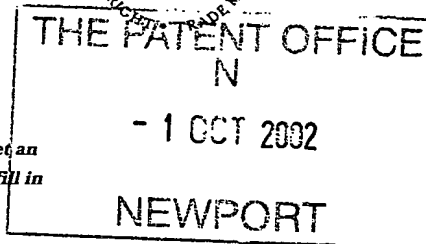
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Patents ADP number (if you know it)

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64108095001

4. Title of the invention

INTEGRATED CIRCUIT

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INTEGRATED CIRCUIT

Field of the Invention

5 The invention relates to an integrated circuit, and in particular, to an integrated circuit having a biasing circuit for maintaining the transconductance of a Gm cell constant.

10 Background of the invention

The transconductance (Gm) of a cell is defined as the ratio of the output current I_{OUT} to the input voltage V_{IN} . The transconductance of a Gm cell on an integrated circuit varies over process and temperature. Depending
15 on the on-chip components used for the cell, this variation can be greater than $\pm 30\%$.

This variation is unacceptable for integrated circuits which rely on a constant transconductance. For
20 example, a constant transconductance is required in order to keep the gain constant in low noise amplifiers (LNAs) having inductive collector loads, or to minimise the variation in the start up gain of a voltage controlled oscillator (VCO). In another example, a
25 constant transconductance is required to minimise frequency error in a constant GmC-filter, such that the variation in the frequency characteristic of the filter frequency is reduced to that due to variation in the capacitors. The variations in capacitance values are
30 usually small compared to the variations in transconductance.

In GmC-filters and gyrator-C circuits, it is known to use an "autotuner" for controlling the tuning frequency of the filter.

5 These circuits use a secondary filter or oscillator using a similar Gm C cell within a control loop, where the frequency of the filter is compared with an external frequency reference to generate an error signal. GB1,421,093 is an example of a GmC-filter
10 having an external frequency reference. US 6,304,135 is another example, in which the GmC-filter uses an external resistor for controlling the frequency. US4,388,539 discloses a constant Gm circuit which, as above, has the disadvantage of requiring the use of a
15 dedicated external resistor for maintaining the transconductance constant.

Thus, all of the known solutions have the disadvantage of requiring an extra external frequency reference or a
20 dedicated external resistor to achieve a constant transconductance, the external frequency reference or resistor being used to fine tune the filter response. The need for an external frequency reference or resistor also has the disadvantage of requiring one or
25 more extra pins on the integrated circuit.

The aim of the present invention is to provide an integrated circuit having a constant Gm biasing circuit which does not have the disadvantages mentioned above.
30

Summary of the invention

According to a first aspect of the invention, there is provided an integrated circuit comprising a biasing circuit for maintaining the transconductance of a Gm

cell constant, the integrated circuit comprising an on-chip constant voltage source and an on-chip constant current source, the on-chip constant current source having a connection for an external resistance, the value of the external resistance determining the current generated by the constant current source, characterised in that the biasing circuit comprises:

means for providing a first fraction (β) of the current generated by the on-chip current source to bias the output of the Gm cell;

means for providing a second fraction (α) of the voltage generated by the on-chip voltage source to bias the input of the Gm cell; and

means for controlling the transconductance of the Gm cell to be equal to the ratio of said fraction of the current generated by the on-chip current source to said fraction of the voltage generated by the on-chip voltage source.

According to another aspect of the invention, there is provided a method of maintaining the transconductance of a Gm cell on an integrated circuit constant, the integrated circuit comprising an on-chip constant voltage source and an on-chip constant current source, the on-chip constant current source having a connection for an external resistance, the value of the external resistance determining the current generated by the constant current source, characterised in that the method comprises the steps of:

providing a first fraction (β) of the current generated by the on-chip current source to bias the output of the Gm cell;

providing a second fraction (α) of the voltage generated by the on-chip voltage source to bias the input of the Gm cell; and

controlling the transconductance of the Gm cell to
 5 be equal to the ratio of said fraction of the current generated by the on-chip current source to said fraction of the voltage generated by the on-chip voltage source.

10 The invention has the advantage that it does not require the use of an external frequency reference, an extra external resistor or any extra external pins.

Brief Description of the drawings

15 For a better understanding of the invention, and to show more clearly how it may be carried into effect, reference will now be made, by way of example, to the accompanying drawings in which:-

Figure 1 shows a typical Gm cell;

20 Figure 2 shows another example of a typical Gm cell;

Figure 3 shows a block diagram of a constant Gm biasing circuit according to the present invention;

Figure 4 shows further details of the constant current source shown in the biasing circuit of Figure 3;

25 Figure 5 shows further details of the constant voltage source shown in the biasing circuit of Figure 1;

Figures 6a shows the Gm transfer characteristic with differential input or with single ended input with the quiescent operating point of the Gm cell defined;

30 Figure 6b shows how the transconductance curve is controlled using a control voltage V_{CNTL} or control current I_{CNTL} ;

Figure 7 shows the application of the invention in a single ended implementation;

Figure 8 shows the application of the invention in a differential implementation.

5 Detailed description of a preferred embodiment of the present invention.

Figure 1 shows a typical Gm cell 1, namely a CMOS inverter comprising first and second transistors 3, 5. The transconductance of such a Gm cell 1 is controlled by controlling the total voltage V_{ctrl} applied across
10 the Gm cell 1.

Figure 2 shows another common type of Gm cell 7, namely a bipolar differential pair configuration comprising transistors 9, 11. The transconductance of the bipolar
15 differential pair configuration 7 is controlled by controlling the bias current I_{ctrl} .

Reference will now be made to how the transconductance of a Gm cell, for example a Gm cell 1, 7 as shown in
20 Figures 1 or 2, is maintained constant in accordance with the invention. It is noted that Figures 1 and 2 give examples of transconductance amplifiers in their simplest forms, and the invention can be applied to any transconductance circuit arrangement, which has means
25 of controlling its transconductance by means of a control voltage or control current.

Figure 3 shows a block diagram of a circuit according to the present invention in which the transconductance
30 of a Gm cell 31 is to be controlled. The constant Gm biasing circuit comprises a constant current source 33, a constant voltage source 35 and an amplifier 37 for introducing loop gain. A voltage V_o is applied to the inverting input of the amplifier 37 to define the

quiescent operating point voltage for the Gm cell 31. If V_0 is applied to the Gm cell 31 no current will flow at the output terminal, and the cell is biased in its quiescent state.

5

According to the invention, the current I_{DC} provided by the constant current source 33 is a fraction of the current from an on-chip current source which is provided on the integrated circuit for other purposes, for example biasing the chip. Furthermore, the voltage V_{DC} provided by the constant voltage source 35 is a fraction of the voltage of an on-chip voltage source which is also provided on the integrated circuit for other purposes.

15

As indicated above, the on-chip constant current source 33 and on-chip constant voltage source 35 are already provided on the integrated circuit for other purposes, for example: setting the input and output DC and signal levels to meet chip to chip interface specifications, eg LVDS and CML output levels; biasing analogue to digital (ADC) and digital to analogue (DAC) converters; or, monitoring of input signal levels or power levels in receiver circuits.

25

The invention has the advantage of enabling the transconductance to be controlled without the need for any external components provided specifically for this purpose.

30

To achieve a constant transconductance over a range of temperature and processes, the on-chip Gm cell 31 requires a means of control, either by applying a voltage or current, depending on the type of Gm cell

being controlled (i.e. a control voltage for a Gm cell 1 as shown in Figure 1, or a control current for a Gm cell 7 as shown in Figure 2). The constant Gm biasing circuit ideally provides a control voltage or current (CTRL) to the on-chip Gm cells to keep their transconductance constant over process and temperature variations.

The transconductance is maintained constant by forcing the transconductance of the Gm cell 31 to be equal to I_{DC}/V_{DC} . This is achieved by controlling the Gm cell's control signal 39 in a loop configuration. As mentioned above, the control signal may be either a control current or a control voltage.

The accuracy of the transconductance of the Gm cell 31 of Figure 3 is determined by the accuracies of the constant current source 33 (I_{DC}) and the constant voltage source 35 (V_{DC}). As mentioned above, the constant current source 33 and the constant voltage source 35 are derived from the respective constant current and constant voltage provided on-chip. Reference will now be made to how the constant current source 33 and constant voltage source 35 are derived from the on-chip current source and on-chip voltage source.

Figure 4 shows in more detail how the constant current source 33 is derived. The on-chip current source 41 is shown in dotted lines and is generated, for example, using a voltage source 43, an amplifier 45 and transistors 47, 49. The on-chip current source 41 also comprises an external resistor 51 which, being an external component, can be chosen to be accurate to

less than 1%, and have a zero temperature coefficient. The resultant current source is therefore largely invariant to, for example, on-chip process and/or temperature variations. The current source is used as
5 a reference for many on-chip circuits as described above.

According to the invention, a circuit 53 is provided for deriving a fraction of the on-chip current source
10 41, for use in the Gm biasing circuit shown in Figure 3. Preferably, the circuit 53 comprises a transistor 55. The fraction β of current taken from the on-chip current source 41 is determined by the ratio of the gain of transistor 47 (say "1") in relation to the gain
15 of transistor 55 (say "m"), ie β is defined as the ratio m:1.

The constant current source 33 (or I_{DC}) for the constant Gm biasing circuit is therefore defined as:
20

$$I_{DC} = \beta \cdot V_{bg} / R_{ext}$$

where V_{bg} is the reference or band gap voltage
25 43 and R_{ext} is the external resistor 51.

As previously mentioned above, it is assumed that the constant current source 33 and its associated external resistor 51 will already be provided on the integrated circuit for other biasing circuits, which means that
30 the constant Gm circuit of the present invention does not require any further external components or extra pins.

Figure 5 shows in greater detail how the constant voltage source 35 (V_{DC}) is preferably derived. The on-chip voltage source 56 is shown in dotted lines, and is already provided on-chip for other purposes as mentioned above, for example fixing the amplitude of ECL logic. It is noted that other circuits could equally be used to provide the on-chip voltage source 56. A voltage reference 43 and an internal resistor 59 are provided to give a process/temperature dependent curve which is then applied to a local resistor 61 of the circuit 58 which is used to derive the fraction of the on-chip voltage source. The local resistor 61 is matched with, but not necessarily equal to, the internal resistor 59. Thus, the current flowing through the matching local resistor 61 cancels out any process or temperature variations. The constant voltage source 5 (or V_{DC}) for use in the constant G_m biasing circuit is taken across points 63, 65 in Figure 5. The constant voltage source 5 (V_{DC}) is a fraction α of the original voltage reference V_{bg}

$$\text{ie } V_{DC} = \alpha \cdot V_{bg}$$

The fraction α is determined by the ratio of the gains of transistors 67, 69, 71, 73 and the ratio of the internal resistors 59, 61, as explained below. First, α is determined by the ratio of the gain of transistor 67 (say "1") in relation to the gain of transistor 69 (say "n"). The ratio of the NMOS transistors 71 and 73 are also set at 1:n so that the current sourced at node 65 by transistor 69 is removed by the NMOS current sink.

Furthermore, by using internal resistors 59, 61 which are of the same type, thus tracking each other over process and temperature, a fraction α of V_{bg} can be generated to provide an absolute bias voltage to the input of the controlled Gm cell within the feedback loop of the control circuit, (V_{bg} being the on-chip band-gap voltage, which is largely independent of process and/or temperature).

Thus, $\alpha = n \cdot R_{61}/R_{59}$, and

$$V_{DC} = (n \cdot R_{61} \cdot V_{bg}) / R_{59}$$

Preferably, the constant-current source 3 and constant-voltage source 5 are derived from the same voltage reference 43. The final controlled transconductance Gm is thereby defined as:

$$G_m = I_{DC}/V_{DC} = \beta/\alpha \cdot 1/R_{ext}$$

This has the advantage that the controlled transconductance is independent of variations or fluctuations in the actual voltage reference 43.

Preferably, the fractions α and β for the biasing circuit are determined according to the type of Gm cell being controlled. In other words, the fractions are chosen such that the transconductance is controlled in a linear region of the transconductance curve for the Gm cell being controlled.

α is chosen such that the Gm cell is operating within its linear range with V_{DC} significantly higher than any input offset variations of the Gm cell which would

cause errors in the setting of the transconductance. The value of β is then determined from the equation:

$$I_{DC} = \beta \cdot V_{bg} / R_{ext}$$

5

$$\text{ie, } \beta = I_{DC} \cdot R_{ext} / V_{bg}$$

Figure 6a shows the transfer function, I_{OUT} against V_{IN} , of a Gm cell with a differential voltage input (or a single ended voltage applied to the quiescent applied voltage). The three curves of the characteristic show the variation of transconductance, defined by the slope, over process and temperature with the controlling element fixed. V_{DC} is the voltage applied at the input of the cell and I_{DC} is the current applied at the output of the cell, which are used to define the transconductance of the cell in its control loop. The transconductance is equal to the slope of the linear region between voltages V_1 and V_2 .

20

Figure 6b shows how the transconductance can be adjusted by the applied control voltage or current, ie V_{ctrl} or I_{ctrl} depending on the type of Gm cell being controlled (as shown in Figures 1 and 2 above). To set the transconductance to the value Gm the control voltage or current would have to be set at values A, B or C for the three curves representing the nominal, and the extremes of process and temperature.

30 A more detailed explanation of the invention will now be given with reference to a single ended implementation and a differential implementation.

Figure 7 shows a single ended implementation of the invention. As mentioned above in relation to Figure 3, the constant Gm biasing circuit comprises a Gm cell 31 having controllable transconductance, a constant
5 current source 33, a constant voltage source 35 and an amplifier 37 introducing loop gain. The aim of the circuit is to force the transconductance of Gm cell 31 to be I_{DC}/V_{DC} . According to this embodiment of a single ended implementation, the biasing circuit comprises a
10 second Gm cell 71. The second Gm cell 71 provides the quiescent DC voltage for the Gm cell 31 being controlled. Alternatively, the dc voltage could be provided using a resistor or other device. The constant transconductance is achieved by providing a
15 control signal 39 to the Gm cells 31 and 71 that keep their transconductance constant over process and temperature, the control signal 39 being either a voltage signal or a current signal, depending on the configuration of the Gm cell.

20 The second Gm cell 71 is of the same type as the first cell 31 and is connected as an active voltage divider with its output current being fed back to its input. The second Gm cell 71 then provides the common mode
25 operating point (voltage) for the first cell 31. With the second cell 71 arranged in this manner at the input of the first cell 31, no DC current will flow into or out from the output of the first Gm cell 31. The DC voltage at "B" at the input of Gm cell 31 will
30 automatically adjust to maintain a zero current state. The constant voltage source 35 (V_{DC}) is provided in series with the voltage at B, which enables the first Gm cell 31 to draw current at its output. Any difference between this current and the applied current

33 produces an error voltage at A, which is amplified by amplifier 37 to produce a control signal 39.

Control signal 39 adjusts the transconductance of both cells 31 and 71 until the voltage at A equals the
5 voltage at B, and the current drawn by cell 31 equals the applied current 33. The transconductance of the first Gm cell 31 is thereby forced to be I_{DC}/V_{DC} .

Since the constant current source 33 and constant
10 voltage source 35 are predetermined fractions of the respective on-chip current and voltage sources, the accuracy of the transconductance is determined by the matching accuracies of the on-chip current source and the on-chip voltage source, and the temperature
15 variation of the on-chip current source's external resistor.

The low input offset of the amplifier 37 forces the voltage at A to be equal to B. The control signal 39
20 can also be used to set the transconductance of other GM cells used elsewhere on-chip, for example, the transconductance amplifiers of GmC-filters, provided that these transconductance amplifiers are identical in design to cell 31. In addition, the control signal 39
25 can also be used to set the transconductance of other Gm cells used elsewhere on-chip, provided the design of such cells is matched with Gm cell 31 to an accurate predefined ratio. This is particularly relevant in the case of CMOS amplifiers of the type shown in Figure 1,
30 where multiple gates, say m, would increase the transconductance by the same ratio. If the transconductance amplifier 31 in Figure 7, for example, has two gate stripes and was set to $50\mu S$ by the control loop, then a similar Gm cell in a GmC filter with ten

stripes would be controlled to be five times $50\mu\text{S}$, ie $250\mu\text{S}$.

Figure 8 shows an embodiment of the invention for a differential implementation. The transconductance of cell 31 is forced to be $I_{\text{DC}}/V_{\text{DC}}$. Additional common mode circuitry, not shown, is used to set the common mode voltage at the input and output of the Gm cell 31. A constant voltage source 35 (V_{DC}), i.e. a fraction of the on-chip voltage source, is applied differentially at the input 63, 65 of the Gm cell 31, which enables it to sink/source current at its output. Any deviation of this current from the applied current I_{DC} produces an error voltage A, which is amplified by amplifier 37 to produce a control signal 39. Control signal 39 adjusts the transconductance of cell 31 until the voltage at A equals the voltage at B, and the current drawn by Gm cell 31 equals the applied current 33. The transconductance of the first Gm cell 31 is thereby forced to be $I_{\text{DC}}/V_{\text{DC}}$.

The differential voltage applied at the input 63, 65 is derived as shown above in relation to Figure 5. The accuracy of the transconductance is determined by the matching accuracies of the constant current source 33 (I_{DC}) and the constant voltage source 35 (V_{DC}), and hence the accuracy of the on-chip current source, on-chip voltage source, and the process and/or temperature variation of the external resistor provided for the on-chip current source.

The invention described above provides a control signal to a Gm cell that ideally makes its transconductance constant over process and temperature variations.

5 The invention enables the transconductance of a Gm cell to be maintained constant using the on-chip voltage source and an on-chip current source and its external resistor, which are already provided on the integrated circuit for other purposes, thereby eliminating the
10 need for any additional external components.

It is noted that the voltages and currents mentioned in the various embodiments can be single ended or differential, depending on implementation.

15

Although the invention has been described in relation to common Gm cells such as a CMOS inverter and a bipolar differential pair, it is noted that the invention is also applicable to other types of Gm
20 cells.

In addition, although the invention has been described in relation to controlling just one Gm cell, it will be readily appreciated that the invention can be used to
25 control a plurality of Gm cells on an integrated circuit.

Preferably, the filter response can be fine tuned using simple internal logic and switches to fine-tune the
30 current I_{DC} in Fig 2 and compensate for any changes in the absolute on-chip capacitance due to process variation.

Since the invention makes use of no external frequency reference for Gm-C filters, it is advantageous over other constant Gm biasing schemes that use external frequency references.

5

The architecture described above can be implemented with CMOS, bipolar, BiCMOS, or other technologies.

CLAIMS

1. An integrated circuit comprising a biasing circuit for maintaining the transconductance of a Gm cell
5 constant, the integrated circuit comprising an on-chip constant voltage source and an on-chip constant current source, the on-chip constant current source having a connection for an external resistance, the value of the external resistance determining the current generated
10 by the constant current source, characterised in that the biasing circuit comprises:
 means for providing a first fraction (β) of the current generated by the on-chip current source to bias the output of the Gm cell;
15 means for providing a second fraction (α) of the voltage generated by the on-chip voltage source to bias the input of the Gm cell; and
 means for controlling the transconductance of the Gm cell to be equal to the ratio of said fraction of
20 the current generated by the on-chip current source to said fraction of the voltage generated by the on-chip voltage source.
2. An integrated circuit as claimed in claim 1,
25 wherein the means for controlling the transconductance comprises a feedback circuit including an amplifier, the amplifier providing a control signal (39) for controlling the transconductance of the Gm cell.
- 30 3. An integrated circuit as claimed in claim 2, wherein the control signal (39) is a current signal.
4. An integrated circuit as claimed in claim 2, wherein the control signal (39) is a voltage signal.

5. An integrated circuit as claimed in any one of the preceding claims, wherein the means for providing a
5 fraction (α) of the on-chip voltage source comprises first and second transistors (68, 69), the first and second transistors having a gain ratio of 1:n.

6. An integrated circuit as claimed in claim 5,
10 wherein the gain n of the second transistor (69) is predetermined according to the transconductance characteristics of the Gm cell being controlled.

7. An integrated circuit as claimed in any one of the
15 preceding claims, wherein the means for providing a fraction (β) of the on-chip current source comprises a transistor (55).

8. An integrated circuit as claimed in claim 7,
20 wherein the gain m of the transistor (55) is chosen according to the transconductance characteristics of the Gm cell being controlled.

9. An integrated circuit as claimed in any one of the
25 preceding claims, wherein the on-chip current source and on-chip voltage source are generated using the same voltage reference, such that the transconductance of the Gm cell is equal to the ratio of the first fraction (β) to the second fraction (α) divided by the value of
30 the external resistor (51).

10. An integrated circuit as claimed in any one of claims 2 to 9, further comprising a second Gm cell, the second Gm cell providing a common mode operating point

voltage at the input of the first Gm cell, the second Gm cell also being controlled by the control signal (39).

5 11. An integrated circuit as claimed in claim 10, wherein the components forming the second Gm cell are matched with the components forming the first Gm cell.

10 12. An integrated circuit as claimed in any one of claims 1 to 9, wherein the fraction (β) of the on-chip current source is connected differentially to the output of the Gm cell, and wherein the fraction (α) of the on-chip voltage source is connected differentially to the input of the Gm cell.

15 13. An integrated circuit as claimed in claim 2, wherein the control signal 39 is also used to control another Gm cell of the same design on the integrated circuit.

20 14. An integrated circuit as claimed in claim 2, wherein the control signal 39 is used to control another Gm cell on the integrated circuit, the design characteristics of the other Gm cell having a
25 predefined ratio to the design characteristics of the first Gm cell.

15. A method of maintaining the transconductance of a Gm cell on an integrated circuit constant, the
30 integrated circuit comprising an on-chip constant voltage source and an on-chip constant current source, the on-chip constant current source having a connection for an external resistance, the value of the external resistance determining the current generated by the

constant current source, characterised in that the method comprises the steps of:

providing a first fraction (β) of the current generated by the on-chip current source to bias the output of the Gm cell;

providing a second fraction (α) of the voltage generated by the on-chip voltage source to bias the input of the Gm cell; and

controlling the transconductance of the Gm cell to be equal to the ratio of said fraction of the current generated by the on-chip current source to said fraction of the voltage generated by the on-chip voltage source.

16. A method as claimed in claim 15, wherein the step of controlling the transconductance comprises providing a feedback circuit including an amplifier, the amplifier providing a control signal (39) for controlling the transconductance of the Gm cell.

17. A method as claimed in claim 16, wherein the control signal (39) is a current signal.

18. A method as claimed in claim 16, wherein the control signal (39) is a voltage signal.

19. A method as claimed in any one of claims 15 to 18, wherein the step of providing a fraction (α) of the on-chip voltage source comprises providing first and second transistors (68, 69) having a gain ratio of 1:n.

20. A method as claimed in claim 19, further comprising the step of setting the gain n of the

transistor (69) according to the transconductance characteristics of the Gm cell being controlled.

21. A method as claimed in any one of claim 15 to 20,
5 wherein the step of providing a fraction (β) of the on-chip current source comprises providing a transistor (55) to generate the fraction (β) of the on-chip current source.

10 22. A method as claimed in claim 21, further comprising the step of setting the gain m of the transistor (55) according to the transconductance characteristics of the Gm cell being controlled.

15 23. A method as claimed in any one of claim 15 to 22, wherein the on-chip current source and on-chip voltage source are generated using the same voltage reference, such that the transconductance of the Gm cell is equal to the ratio of the first fraction (β) to the second
20 fraction (α) divided by the value of the external resistor (51).

24. A method as claimed in any one of claims 16 to 23, further comprising the step of providing a second Gm
25 cell, the second Gm cell providing a common mode operating voltage to the input of the first Gm cell, the second Gm cell also being controlled by the control signal (39).

30 25. A method as claimed in claim 24, further comprising the step of matching the components forming the second Gm cell with the components forming the first Gm cell.

26. A method as claimed in any one of claims 15 to 23, further comprising the step of connecting the fraction (β) of the on-chip current source differentially to the output of the Gm cell, and connecting the fraction (α) of the on-chip voltage source differentially to the input of the Gm cell.
27. A method as claimed in claim 16, wherein the control signal 39 is also used to control another Gm cell of the same design on the integrated circuit.
28. A method as claimed in claim 16, wherein the control signal 39 is used to control another Gm cell on the integrated circuit, the design characteristics of the other Gm cell having a predefined ratio to the design characteristics of the first Gm cell.

ABSTRACT

INTEGRATED CIRCUIT

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An integrated circuit comprises a biasing circuit for maintaining the transconductance of a Gm cell constant. The integrated circuit comprises an on-chip constant voltage source and an on-chip constant current source.

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The on-chip constant current source has a connection for an external resistance, the value of the external resistance determining the current generated by the constant current source. The biasing circuit comprises means for providing a first fraction (β) of the current

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generated by the on-chip current source to bias the output of the Gm cell, and means for providing a second fraction (α) of the voltage generated by the on-chip voltage source to bias the input of the Gm cell. The transconductance of the Gm cell is controlled to be

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equal to the ratio of said fraction of the current generated by the on-chip current source to said fraction of the voltage generated by the on-chip voltage source.

25 *Figure 3 to accompany abstract*



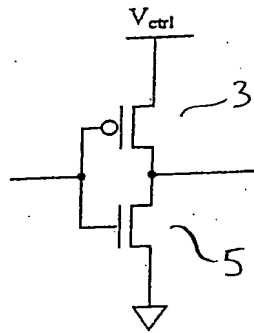


FIGURE 1

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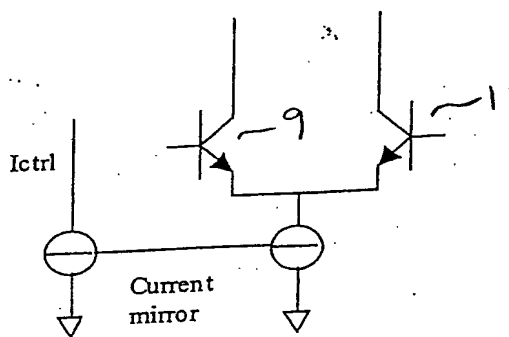


FIGURE 2

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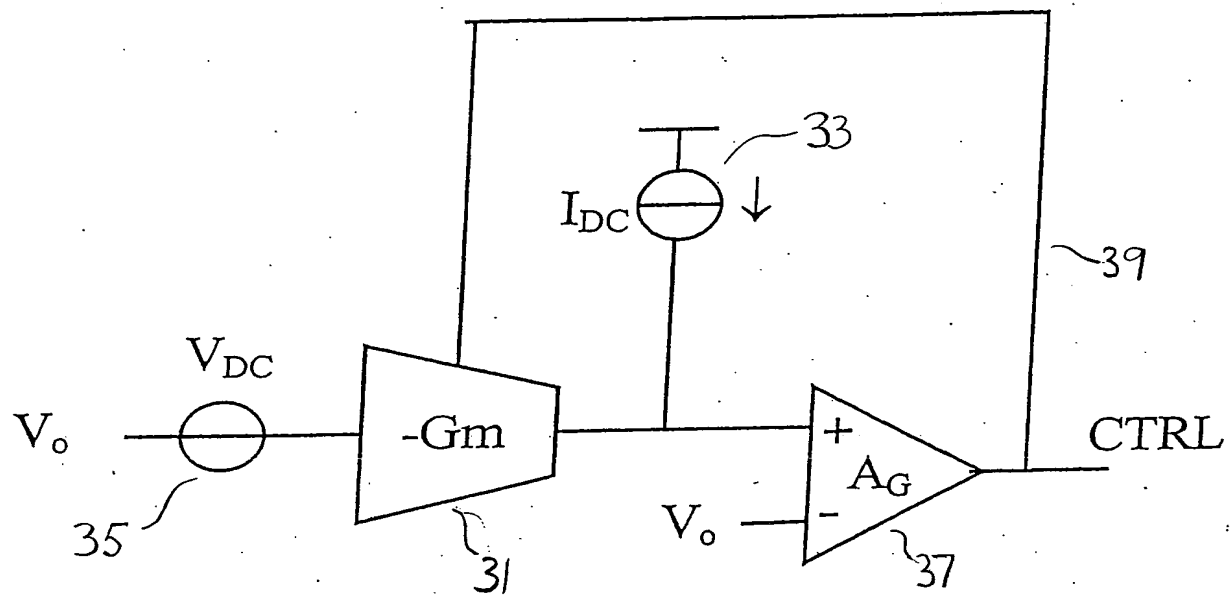


FIGURE 3

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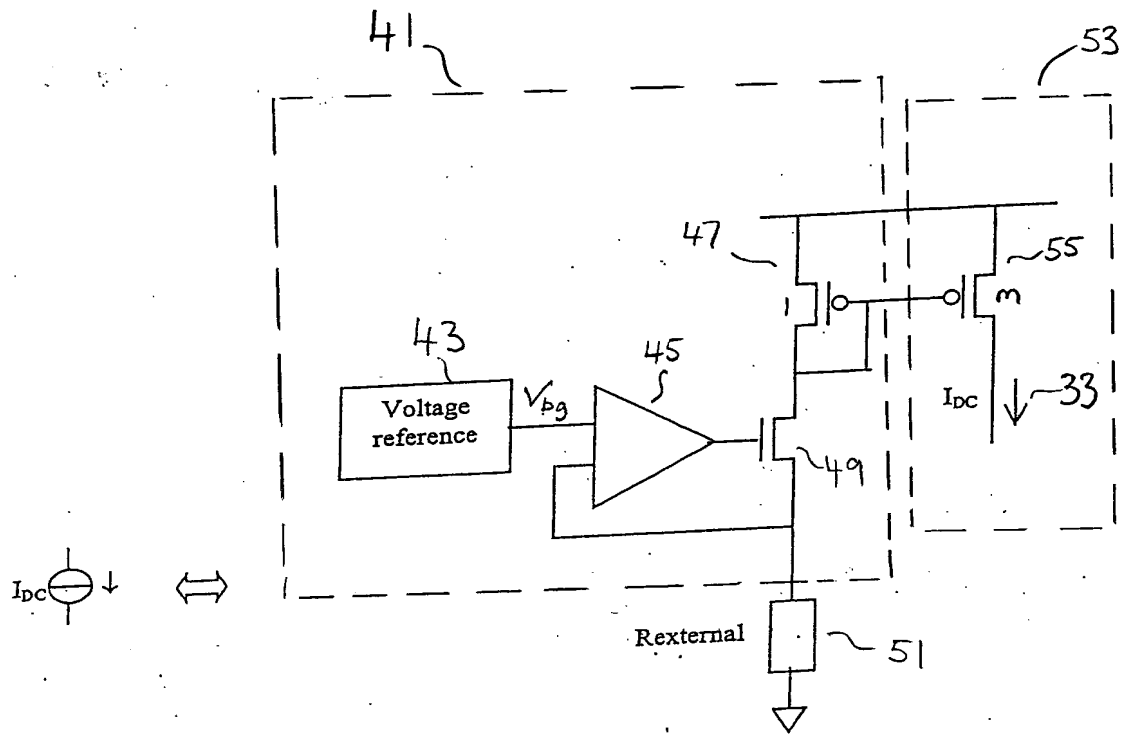


FIGURE 4

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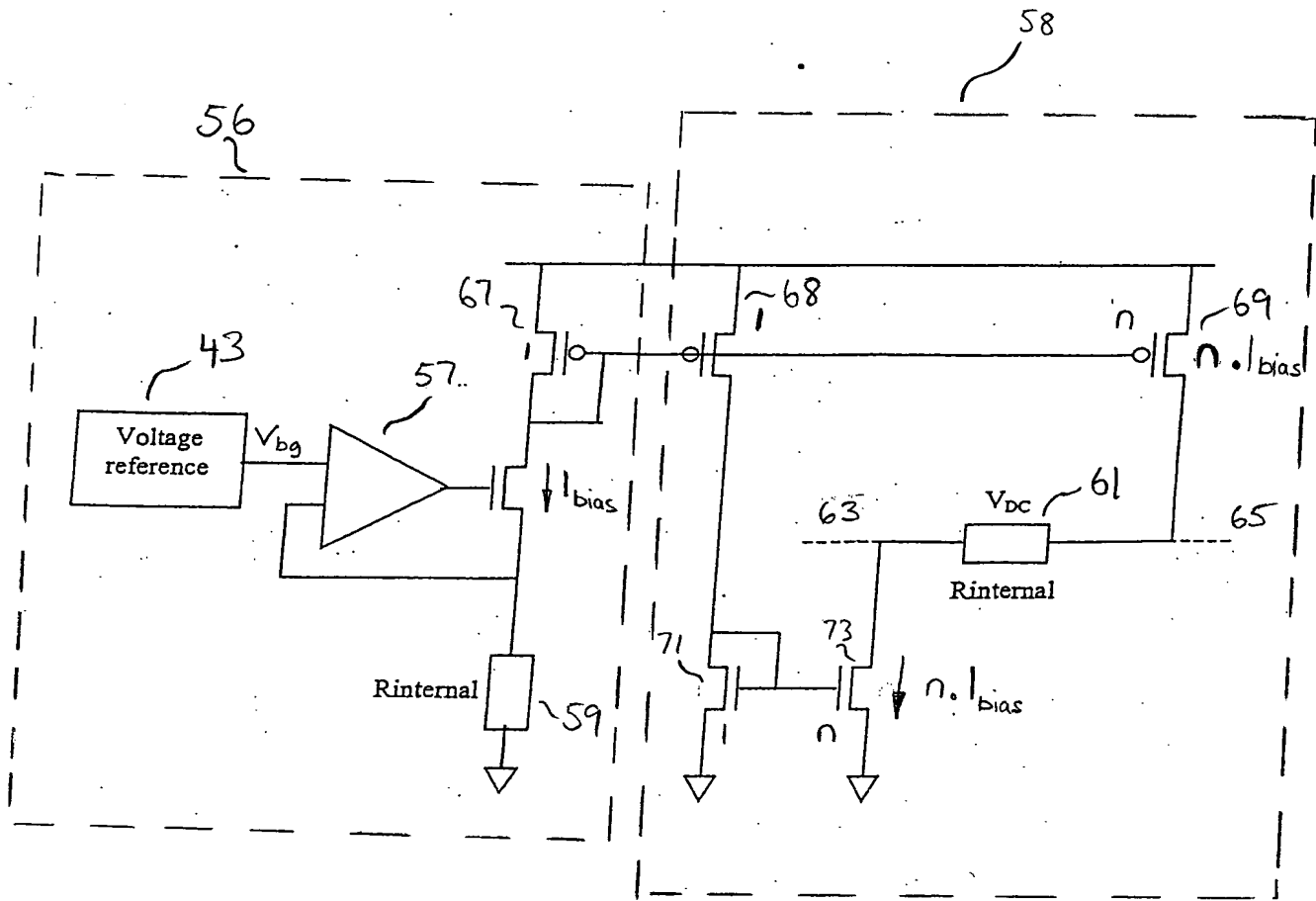


FIGURE 5

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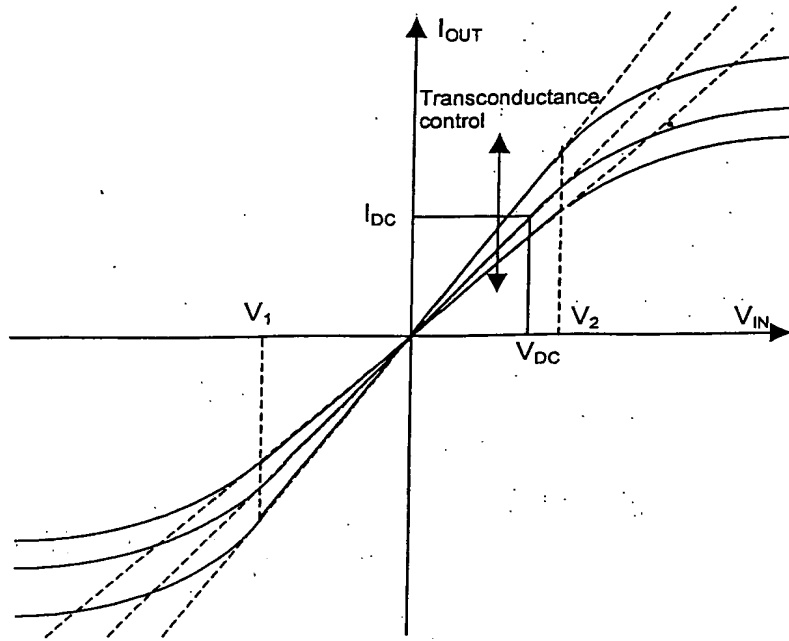


FIG. 6A

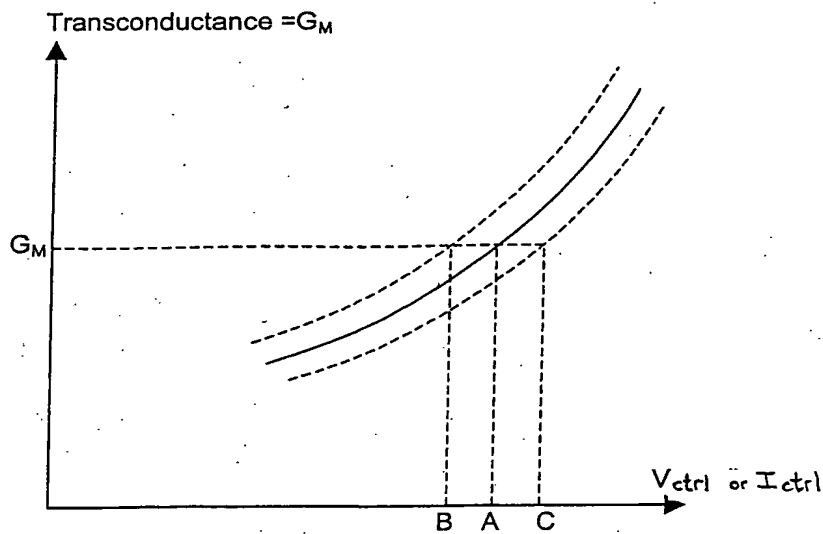


FIG 6B

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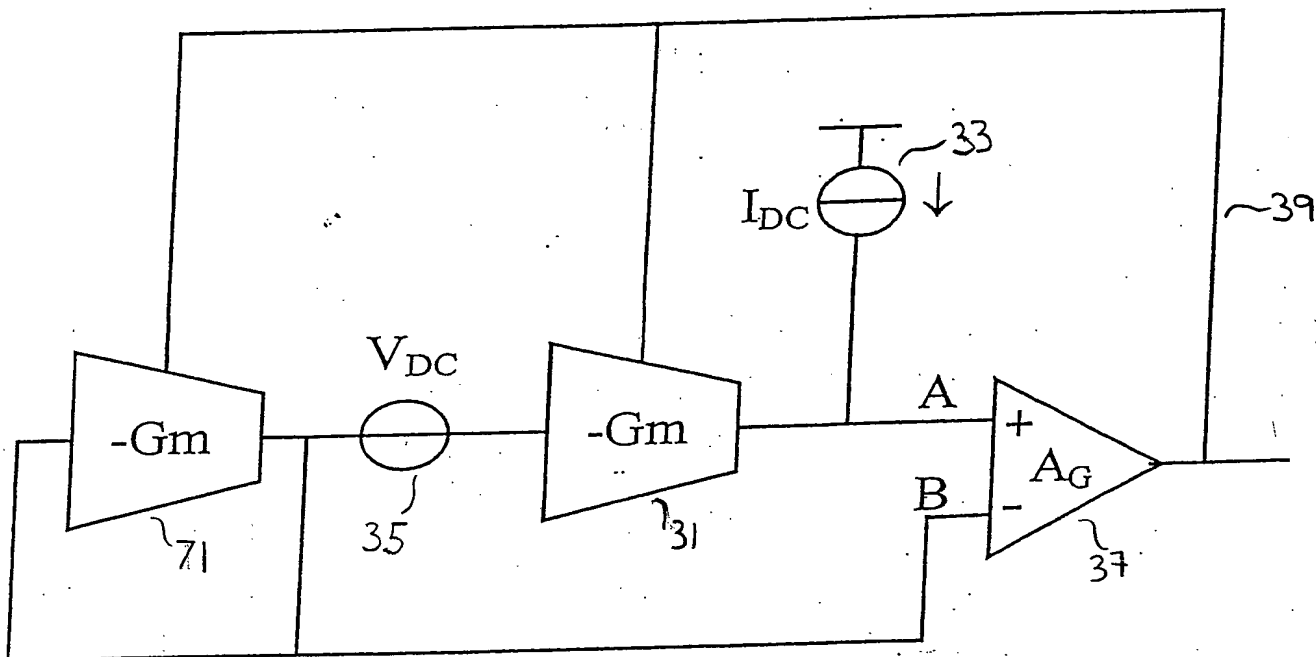


FIGURE 7

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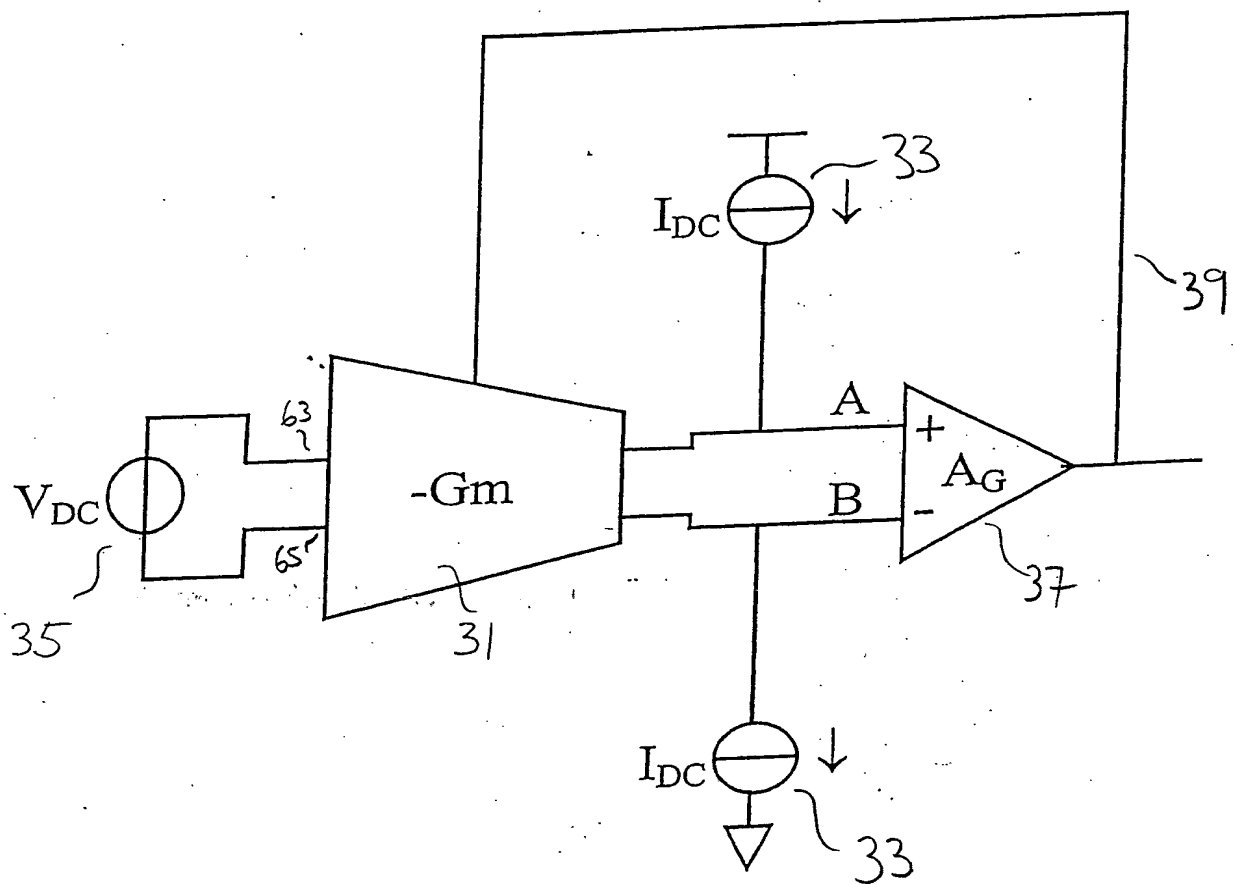


FIGURE 8

Application No. 10/673,566
Attorney Docket No. 027557-106
Burns, Doane, Swicker + Mathis
703-836-6620

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